

## MGPURST Bachelor of Science (B.Sc.) Sem-IV Examination

## PHYSICS

## Paper-II

## (Solid State Electronics &amp; Molecular Physics)

Time—Three Hours]

[Maximum Marks—50

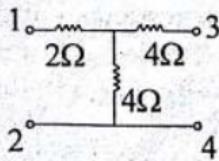
- Note :-**
- (i) All questions are compulsory.
  - (ii) Draw well labelled diagram wherever necessary.

**EITHER**

1. (A) What is transistor ? Explain the input and output characteristics of NPN transistor in CE mode with neat circuit diagram. 5
- (B) (i) Explain the construction and working of a light emitting diode. 3
- (ii) Calculate the wavelength in  $\text{A}^\circ$  of a light emitted by LED if the band gap is 3eV.  
Given  $h = 6.626 \times 10^{-34} \text{ J-S}$ ,  
 $c = 3 \times 10^8 \text{ m/s}$  and  $1\text{eV} = 1.6 \times 10^{-19} \text{ J}$ . 2

**OR**

- (C) Explain the factors that affect the operating point of a transistor. 2½
- (D) Find the h-parameters of the circuit shown in figure. 2½



- (E) Give the construction and working of photovoltaic cell. 2½
- (F) Draw the equivalent circuit of transistor at low frequency in CE mode and explain in brief. 2½

**EITHER**

2. (A) Draw the circuit diagram of JFET as an amplifier with input and output waveforms. Derive an expression for the input and output impedance and voltage gain of an amplifier.
- (B) (i) Explain the drain characteristics of n-channel depletion MOSFET when (i)  $V_{GS}$  is negative and (ii)  $V_{GS}$  is positive. 3
- (ii) In the drain characteristics of MOSFET,  $AI_D = 2 \text{ mA}$  when  $\Delta V_{DS} = 10 \text{ volts}$  at constant  $V_{GS} = 3 \text{ V}$ . Calculate the output impedance. 2

**OR**

- (C) Draw the output characteristics of JFET and explain different regions in it. 2½
- (D) Calculate the transconductance of JFET with change in drain current 4mA and change in gate to source voltage 0.4 V when drain to source voltage is constant. Hence find the amplification factor if drain resistance is  $47 \text{ k}\Omega$ . 2½
- (E) Explain JFET as an amplifier with neat diagram. 2½
- (F) State the difference between BJT and JFETS. 2½

**EITHER**

3. (A) Derive an expression for rotational energy of diatomic molecule and explain why diatomic molecule in ground state can not rotate. 5



(B)

- (i) Obtain an expression for frequency of pure vibrational spectra of a molecule. 3
- (ii) Calculate the wave number of the spectral line if change in energy in vibrational energy level is 0.1 eV. 2

**OR**

- (C) The OH radical has moment of inertia  $1.48 \times 10^{-47} \text{ kg m}^2$ , calculate its inter nuclear distance (Given  $m_H = 1.67 \times 10^{-27} \text{ kg}$ ,  $m_O = 26.72 \times 10^{-27} \text{ kg}$ ). 2½
- (D) Discuss in short failure of Born-Oppenheimer approximation. 2½
- (E) Assuming the equation of energy of unharmonic vibration of a molecule, derive the expression for wave number of unharmonic vibrator in  $V^{\text{th}}$  eigen state. 2½
- (F) Discuss vibration-rotation spectra of diatomic molecule with energy level diagram in brief. 2½

**EITHER**

4. (A) What is Raman Effect ? Give the experimental set up with diagram to obtain Raman Spectrum of a given sample. 5
- (B) (i) Discuss the quantum mechanical explanation of Raman Effect. 3
- (ii) The wavelength of an exciting line in a Raman experiment is  $5460 \text{ A}^{\circ}$  and Stokes line is at  $5520 \text{ A}^{\circ}$ . Find Raman shift ( $c = 3 \times 10^8 \text{ m/s}$ ). 2

**OR**

- (C) Explain the working of NMR spectrometer with a block diagram. 2½

(D) State and explain Franck-Condon principle for the intensity distribution. 2½

(E) What are the applications of ESR spectroscopy ? 2½

(F) The vibrational spectrum of  $O_2$  molecules has a continuum limit of  $56875\text{ cm}^{-1}$ . The upper electronic state dissociates into one ground state atom and one excited atom whose energy from atomic spectrum is  $15875\text{ cm}^{-1}$ . Estimate the dissociation.

Given :  $h = 6.63 \times 10^{-34}\text{ J.S}$ ,  $c = 3 \times 10^{10}\text{ cm/s}$   
 Avag. Number =  $6.03 \times 10^{23}\text{ joule/mole}$ .

2½

5. Solve any TEN (1 mark each) :

- (i) Why is base thin and lightly doped in transistor ?
- (ii) In CB mode, the transistor has an  $\alpha = 0.9$ , determine collector current  $I_c$  if emitter current  $I_E = 1\text{ mA}$ .
- (iii) What is heat sink ? State its necessity.
- (iv) The MOSFET is also called IGFET, why ?
- (v) What are FET's parameter ?
- (vi) State the advantages of FETS over BJTS.
- (vii) Draw the energy diagram of rotational spectra of diatomic molecule.
- (viii) Calculate the spacing between vibrational energy level for frequency of vibration  $2.04 \times 10^{13}\text{ Hz}$ .
- (ix) State the selection rules for vibrational spectra.
- (x) What is meant by heat of dissociation ?
- (xi) Why LASER source is most suitable to study Raman effect ?
- (xii) Calculate the wave number of Raman line of wavelength  $4358\text{ \AA}$ . 1×10